

MiniSKiiP<sup>®</sup> 2

3-phase bridge rectifier + brake chopper + 3-phase bridge inverter SKIIP 24NAB126V10

#### Features

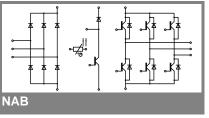
- Fast Trench IGBTs
- Robust and soft freewheeling diodes in CAL technology
- Highly reliable spring contacts for electrical connections
- UL recognised file no. E63532

#### **Typical Applications\***

- Inverter up to 19 kVA
- Typical motor power 11 kW

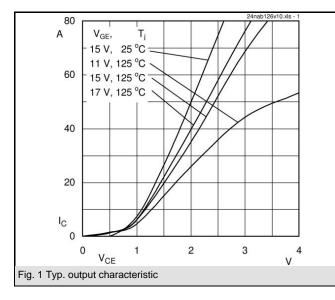
#### Remarks

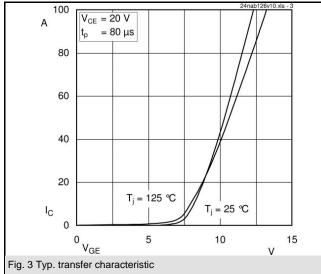
• V<sub>CEsat</sub> , V<sub>F</sub> = chip level value

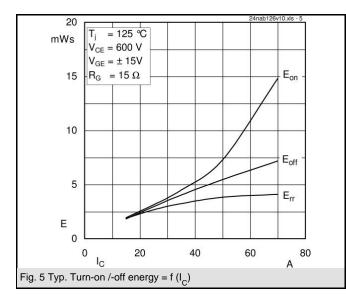


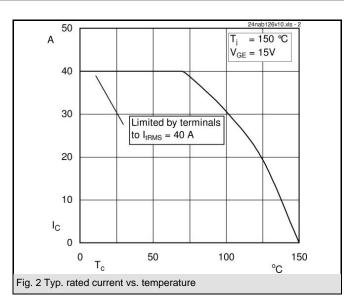
Absolute	Maximum Ratings	$T_s$ = 25 °C, unless otherwise specified						
Symbol	Conditions	Values						
IGBT - Inverter, Chopper								
V <sub>CES</sub>		1200	V					
I <sub>C</sub>	T <sub>s</sub> = 25 (70) °C	52 (40)	Α					
I <sub>CRM</sub>		70	Α					
V <sub>GES</sub>		± 20	V					
Т <sub>ј</sub>		- 40 + 150	°C					
Diode - Inverter, Chopper								
I <sub>F</sub>	T <sub>s</sub> = 25 (70) °C	38 (29)	Α					
I <sub>FRM</sub>		70	А					
т <sub>ј</sub>		- 40 + 150	°C					
Diode - Rectifier								
V <sub>RRM</sub>		1600	V					
I <sub>F</sub>	T <sub>s</sub> = 70 °C	61	Α					
I <sub>FSM</sub>	t <sub>p</sub> = 10 ms, sin 180 °, T <sub>i</sub> = 25 °C	700	А					
i²t	t <sub>p</sub> = 10 ms, sin 180 °, T <sub>j</sub> = 25 °C	2400	A²s					
Т <sub>ј</sub>		- 40 + 150	°C					
Module								
I <sub>tRMS</sub>	per power terminal (20 A / spring)	40	А					
T <sub>stg</sub>		- 40 + 125	°C					
V <sub>isol</sub>	AC, 1 min.	2500	V					

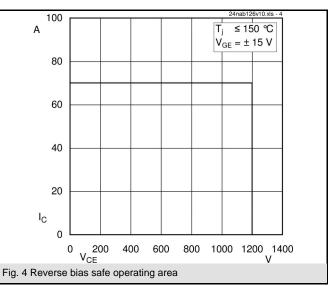
Characteristics T <sub>s</sub> = 25 °C, unless otherwise specifie						
Symbol	Conditions	min.	typ.	max.	Units	
IGBT - In	verter, Chopper					
V <sub>CEsat</sub>	I <sub>Cnom</sub> = 35 A, T <sub>j</sub> = 25 (125) °C		1,7 (2)	2,1 (2,4)	V	
V <sub>GE(th)</sub>	$V_{GE} = V_{CE}, I_{C} = 1,5 \text{ mA}$	5	5,8	6,5	V	
V <sub>CE(TO)</sub>	T <sub>j</sub> = 25 (125) °C		1 (0,9)	1,2 (1,1)	V	
r <sub>T</sub>	T <sub>j</sub> = 25 (125) °C		20 (31)	26 (37)	mΩ	
C <sub>ies</sub>	$V_{CE} = 25 \text{ V}, \text{ V}_{GE} = 0 \text{ V}, \text{ f} = 1 \text{ MHz}$		2,4		nF	
C <sub>oes</sub>	$V_{CE} = 25 \text{ V}, V_{GE} = 0 \text{ V}, \text{ f} = 1 \text{ MHz}$		0,5		nF	
C <sub>res</sub>	V <sub>CE</sub> = 25 V, V <sub>GE</sub> = 0 V, f = 1 MHz		0,3		nF	
R <sub>th(j-s)</sub>	per IGBT		0,75		K/W	
t <sub>d(on)</sub>	under following conditions		80		ns	
t <sub>r</sub>	$V_{CC} = 600 \text{ V}, V_{GE} = \pm 15 \text{ V}$		30			
t <sub>d(off)</sub>	I <sub>Cnom</sub> = 35 A, T <sub>j</sub> = 125°C		410		ns	
t <sub>f</sub>	$R_{Gon} = R_{Goff} = 15 \Omega$		120			
E <sub>on</sub>	inductive load		4,6		mJ	
E <sub>off</sub>			4		mJ	
Diode - Ir	verter, Chopper					
V <sub>F</sub> = V <sub>EC</sub>	I <sub>Fnom</sub> = 35 A, T <sub>i</sub> = 25 (125) °C		1,8 (1,8)	2,1 (2,2)	V	
V <sub>(TO)</sub>	T <sub>i</sub> = 25 (125) °C		1 (0,8)	1,1 (0,9)	V	
r <sub>T</sub>	T <sub>i</sub> = 25 (125) °C		23 (31)	29 (37)	mΩ	
R <sub>th(j-s)</sub>	per diode		1,5		K/W	
I <sub>RRM</sub>	under following conditions		43		Α	
Q <sub>rr</sub>	I <sub>Enom</sub> = 35 A, V <sub>R</sub> = 600 V		7		μC	
Err	V <sub>GE</sub> = 0 V, T <sub>i</sub> = 125 °C		3,3		mJ	
	di <sub>F</sub> /dt = 1450 A/µs					
Diode -R	ectifier	ł			-	
V <sub>F</sub>	I <sub>Fnom</sub> = 35 A, T <sub>i</sub> = 25 °C		1,1		V	
V <sub>(TO)</sub>	T <sub>i</sub> = 150 °C		0,8			
r <sub>T</sub>	T <sub>i</sub> = 150 °C		11			
R <sub>th(j-s)</sub>	per diode		0,9			
	ture Sensor				1	
R <sub>ts</sub>	3 %, T <sub>r</sub> = 25 (100) °C		1000(1670)		Ω	
Mechanio	cal Data				_1	
w			65		g	
Ms	Mounting torque	2		2,5	Nm	

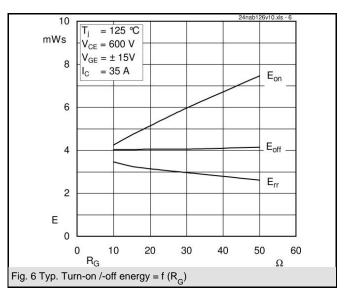


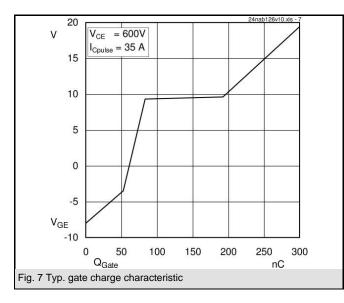


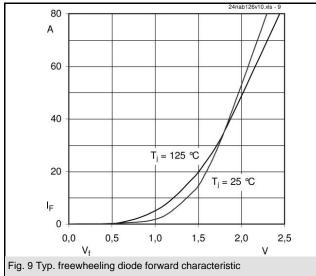


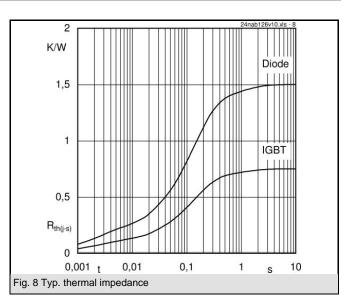


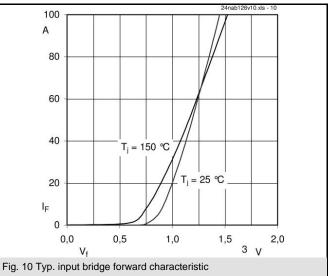




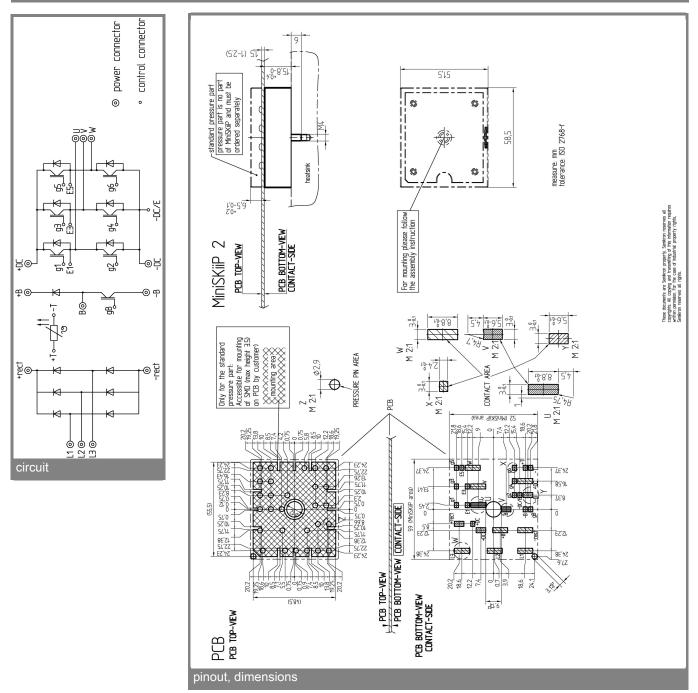








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This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

\* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.

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